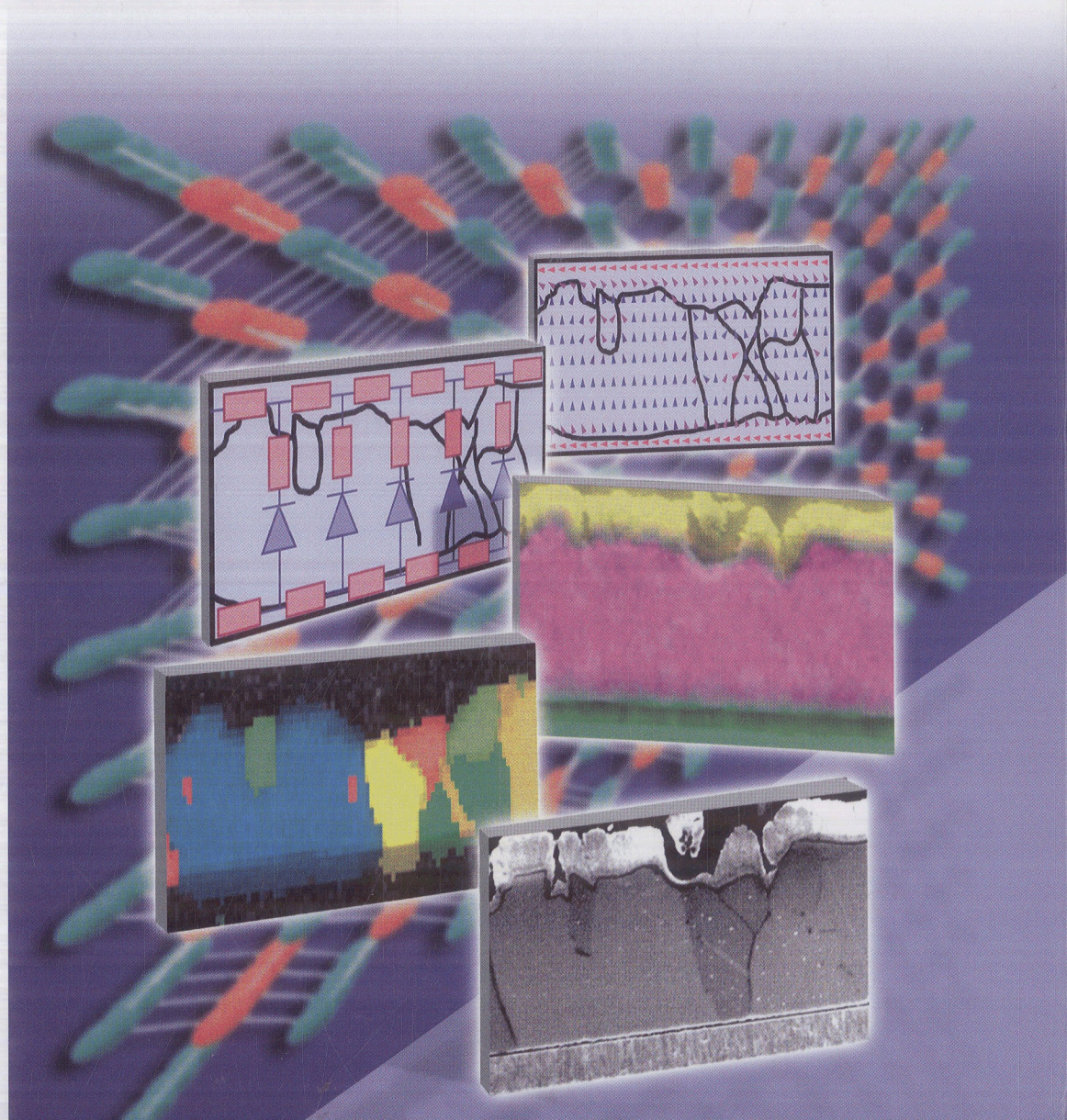


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 WILEY-VCH

# Advanced Characterization Techniques for Thin Film Solar Cells



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